

FIG. 1

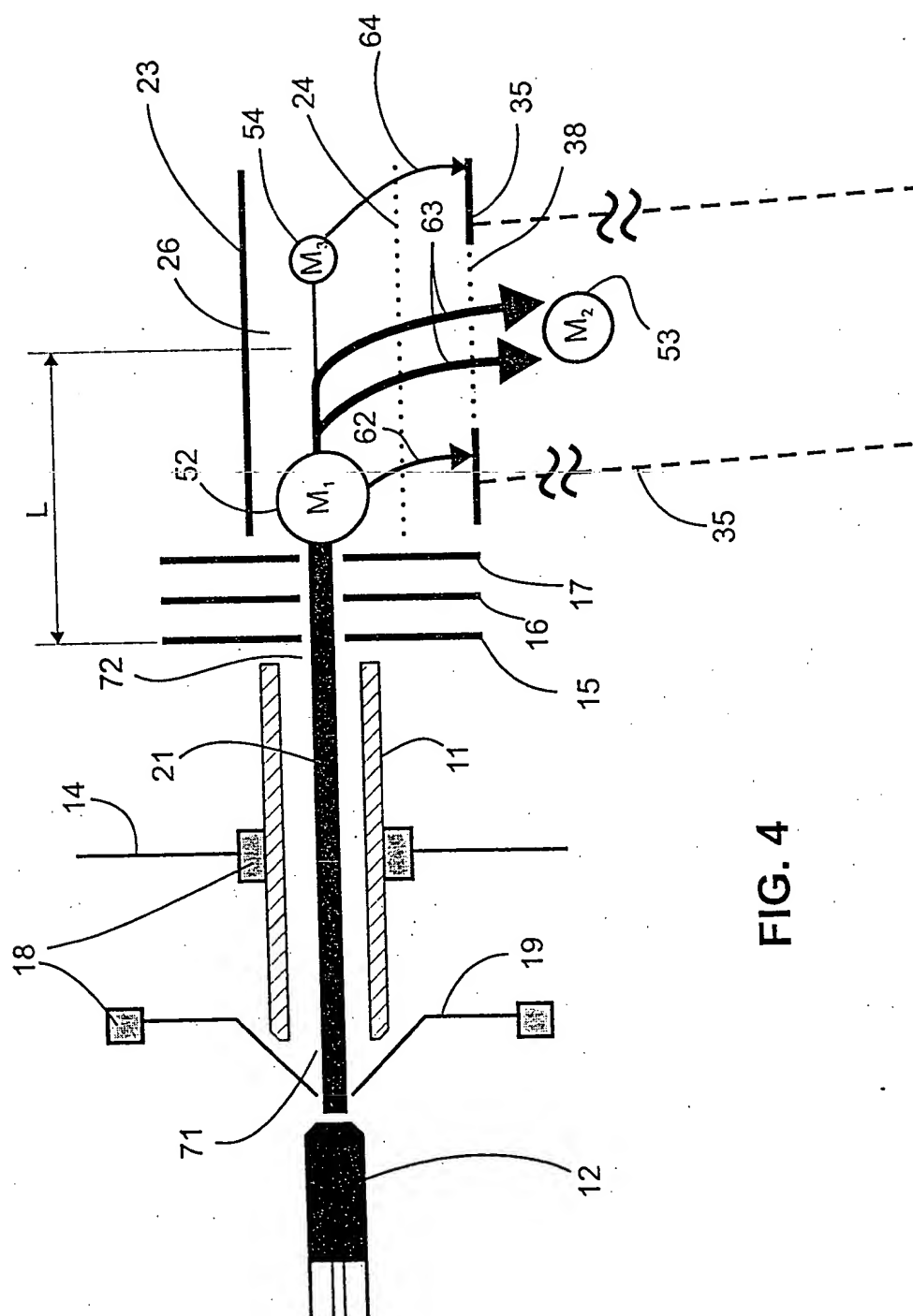
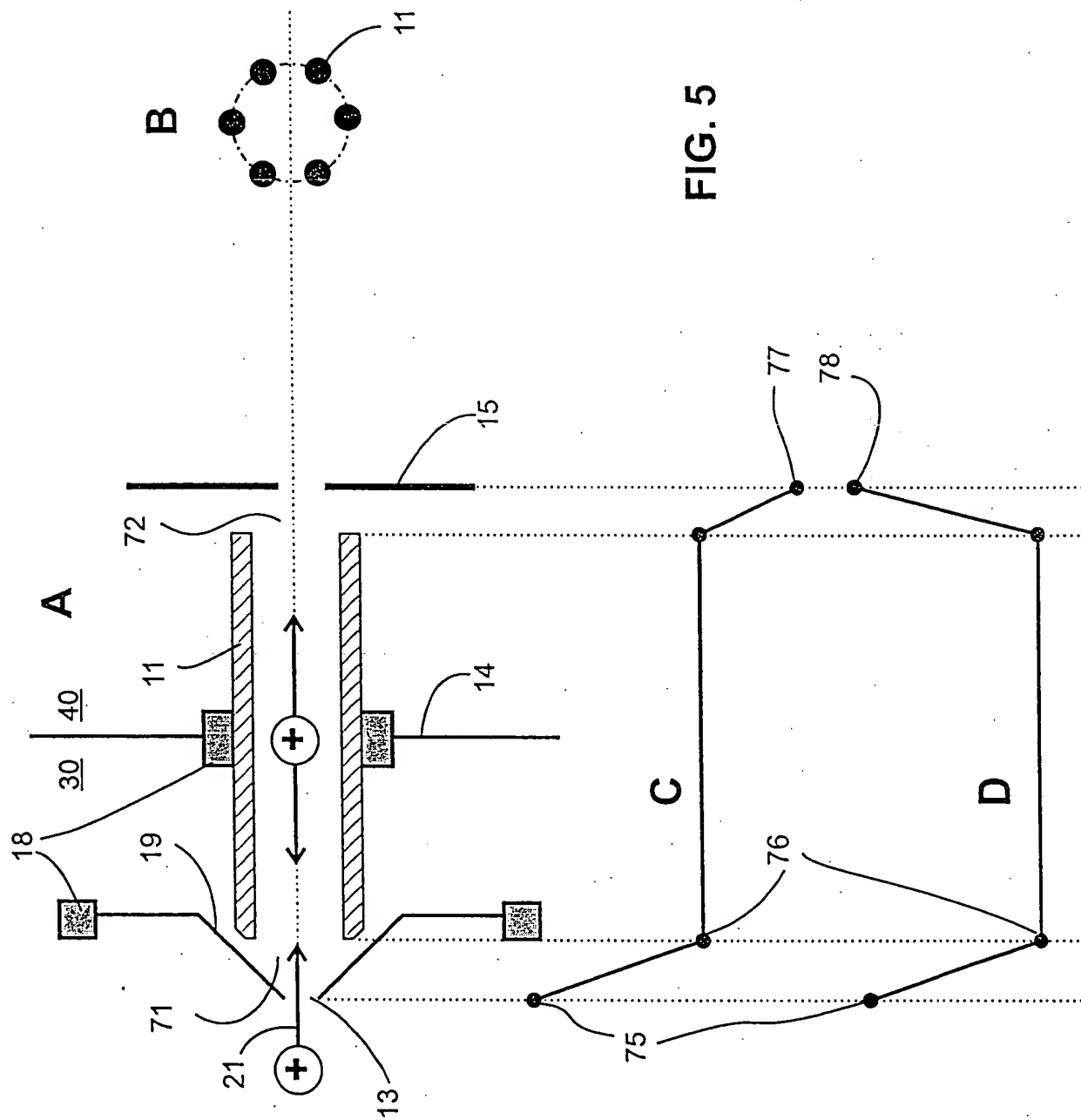


FIG. 4



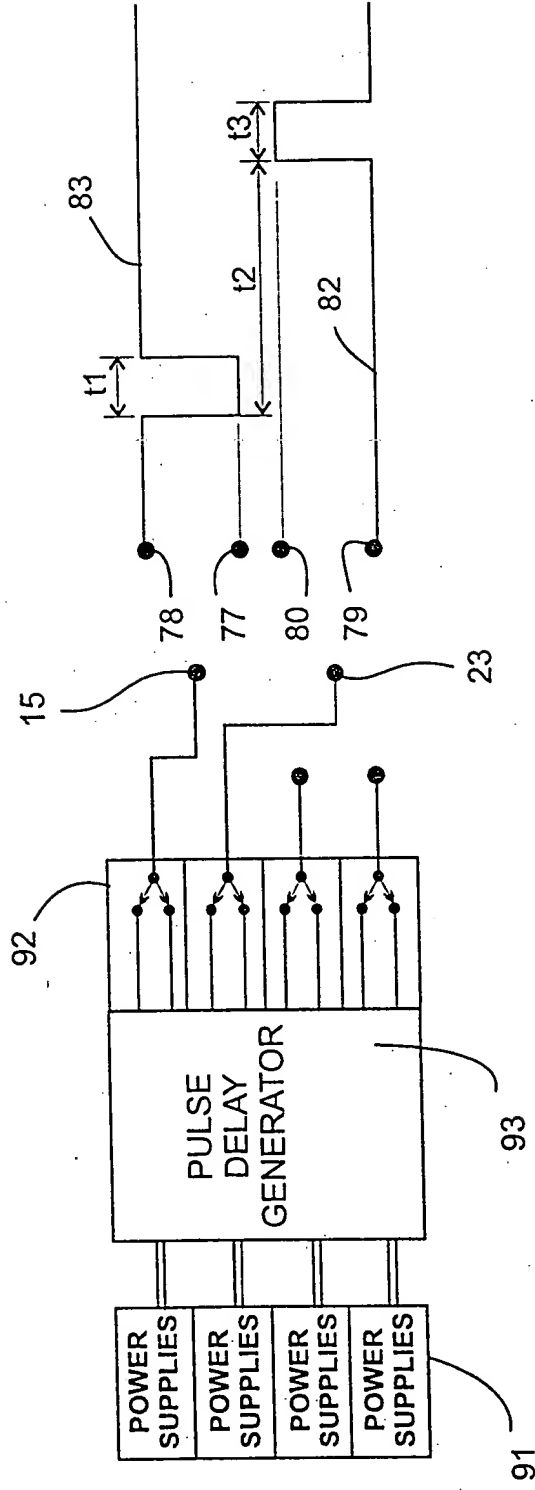


FIG. 6

REF ID: A9430350

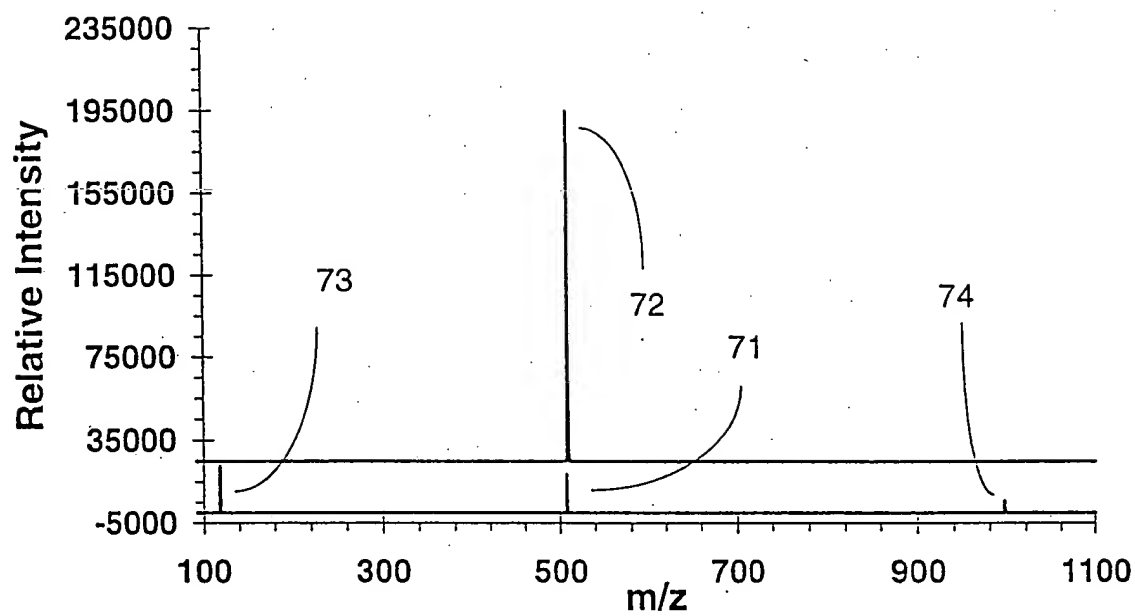


FIG. 7A

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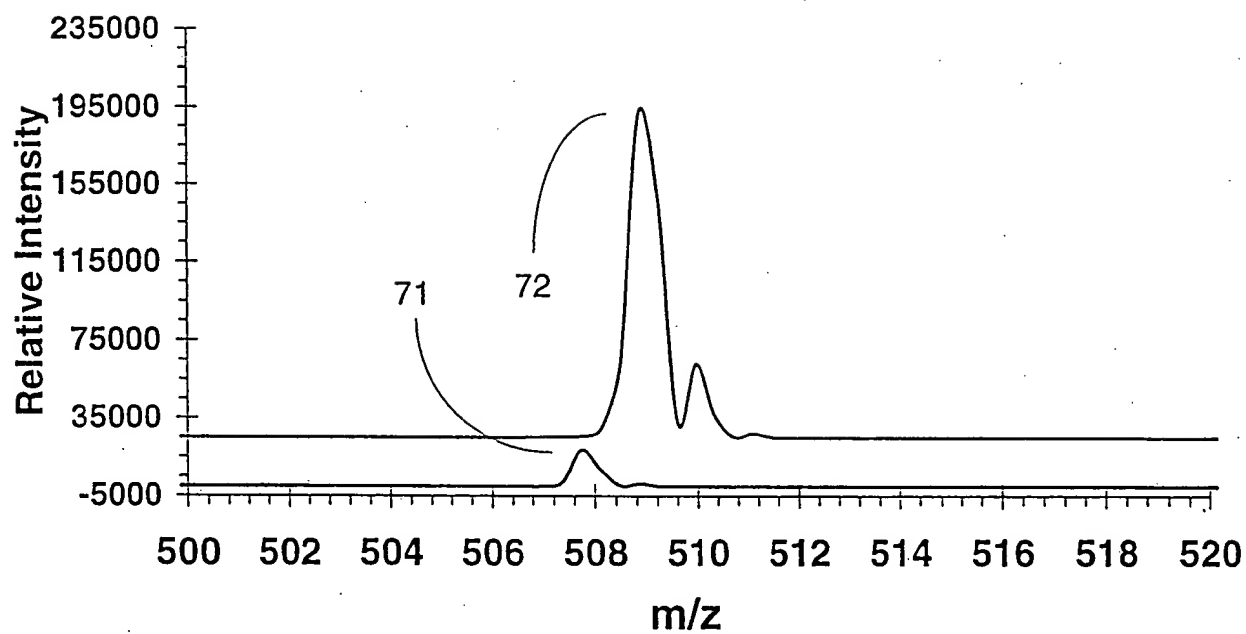


FIG. 7B

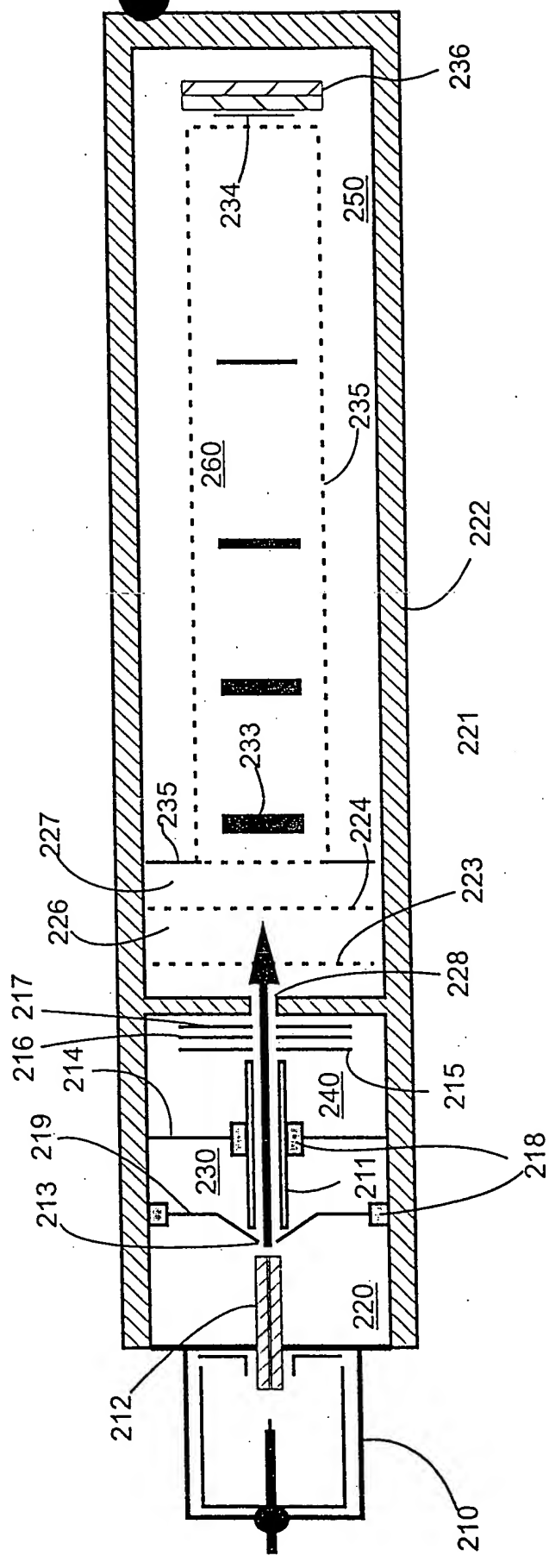
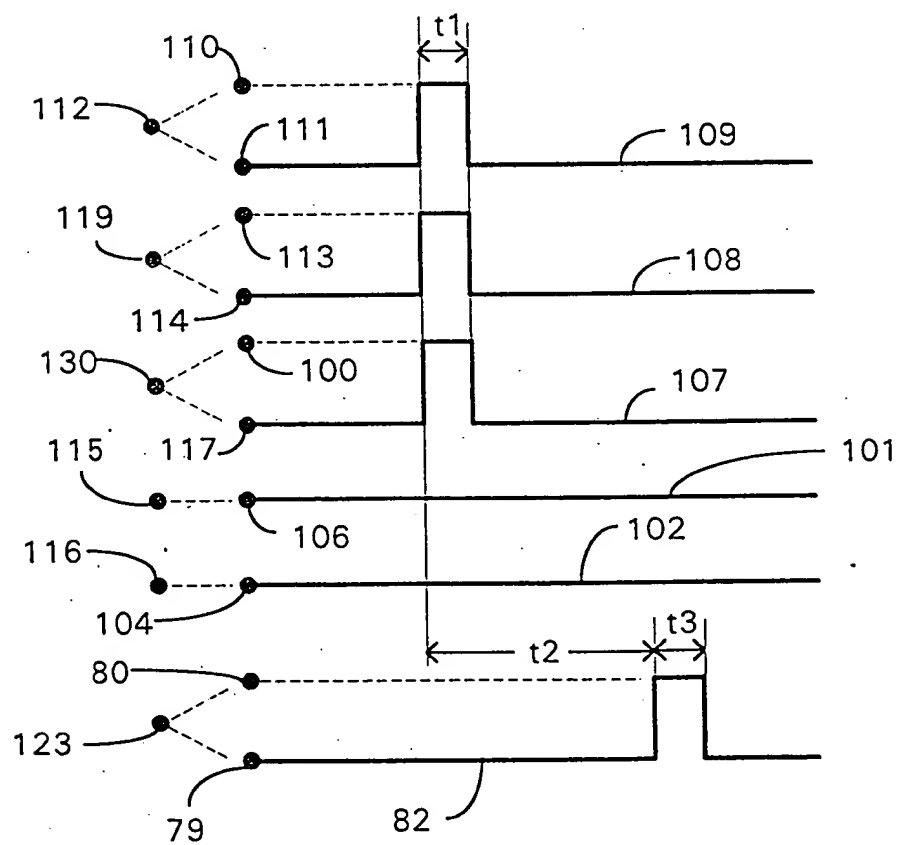


FIG. 8

[illegible]

A

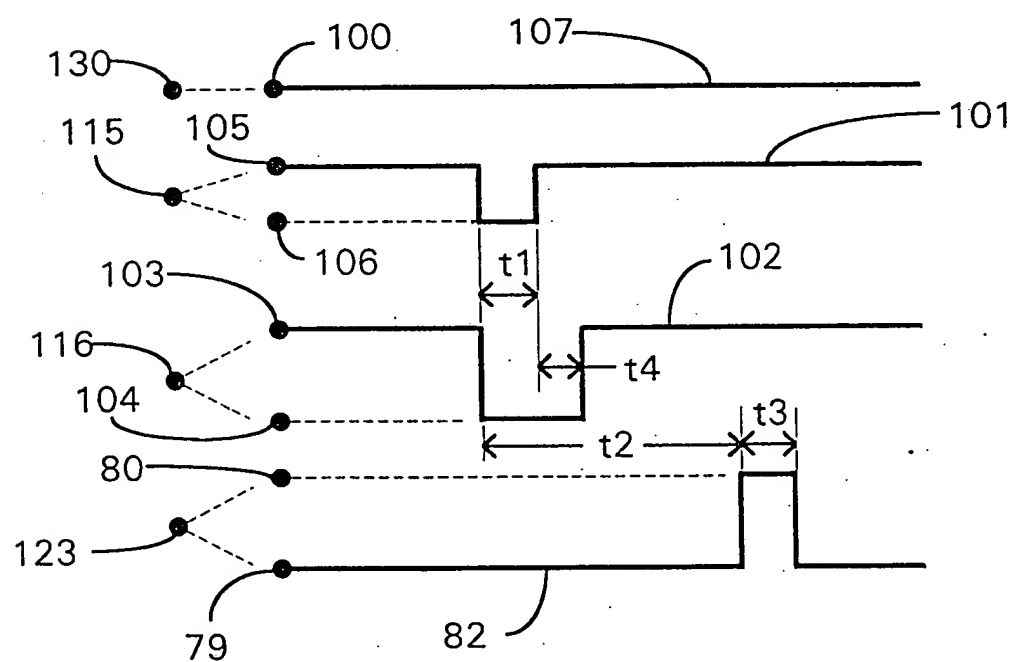


B

FIG. 9

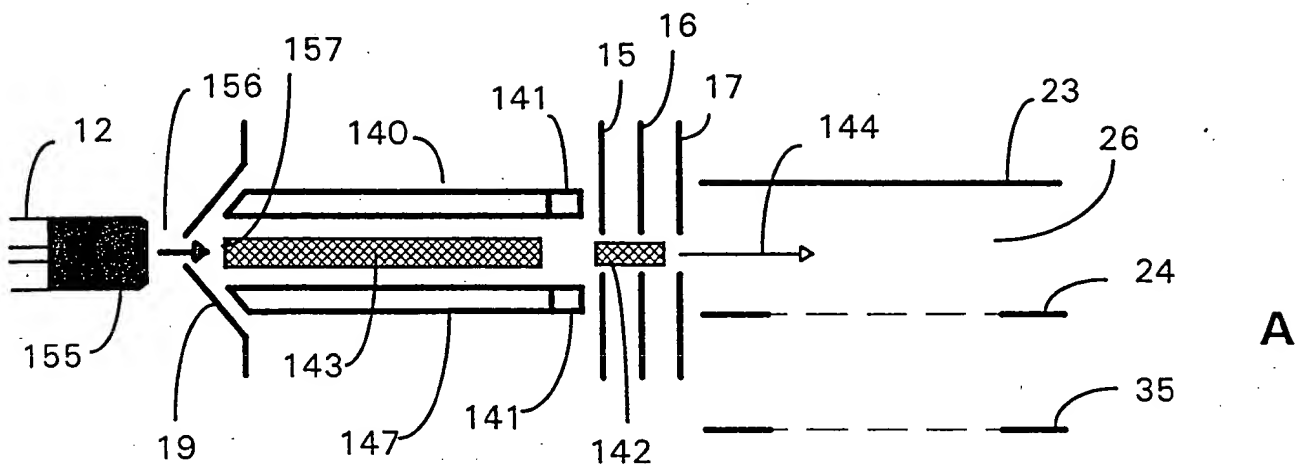
A cross-sectional view of a semiconductor device. The structure consists of several layers and regions. At the top is a layer labeled 107. Below it is a layer labeled 101. A central region is labeled 102. To the left of the central region, there are several layers and regions: 100, 105, 106, 103, 116, 104, 80, and 123. A layer labeled 79 is at the bottom left. A layer labeled 82 is at the bottom right. Dimensions are indicated: t_1 is the thickness of a layer, t_2 is the width of a region, and t_3 is the width of a region. Various points are labeled with numbers: 130, 115, 105, 106, 103, 116, 104, 80, and 123. Dashed lines connect these points to their corresponding locations in the structure.

A

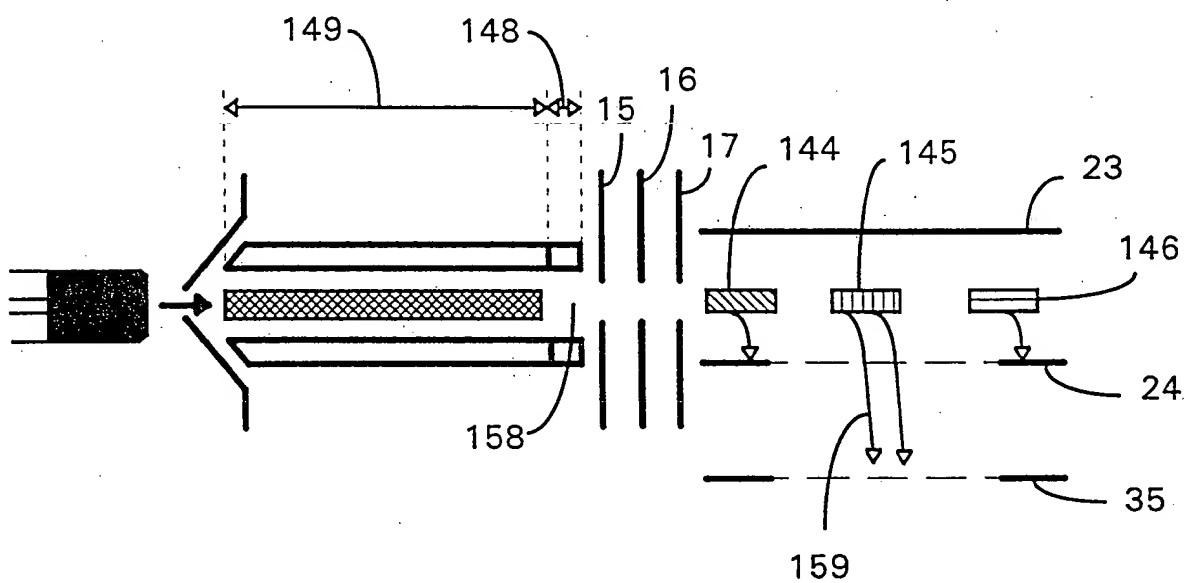


B

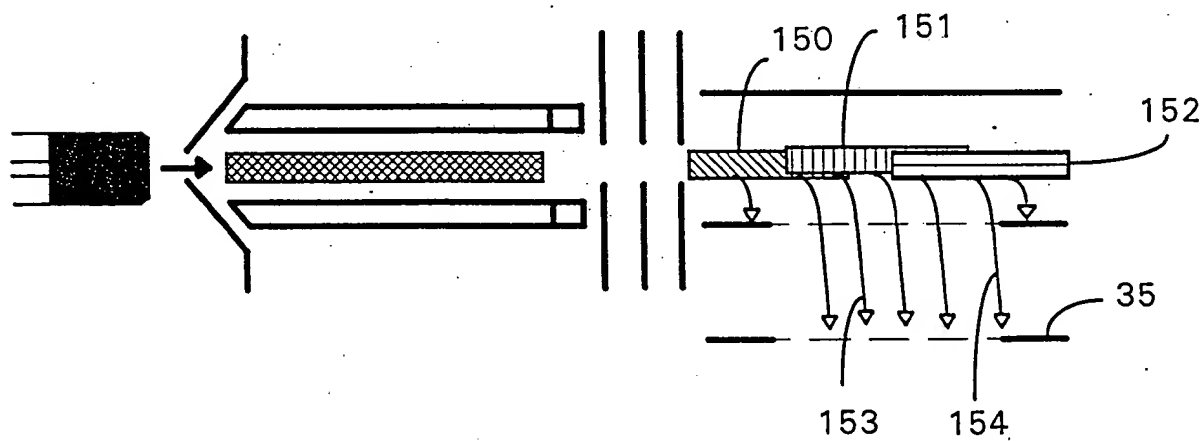
FIG. 10



A



B



C

FIG. 11